

# SANYO Semiconductors

## DATA SHEET



### N-Channel Silicon MOSFET MCH3474 — General-Purpose Switching Device **Applications**

#### **Features**

- · Low ON-resistance.
- Ultrahigh speed switching.
- 1.8V drive.

#### **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		30	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		4	A
Drain Current (Pulse)	IDP	PW⊴10µs, duty cycle≤1%	16	A
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =2A	2.0	3.4		S

Marking : FF

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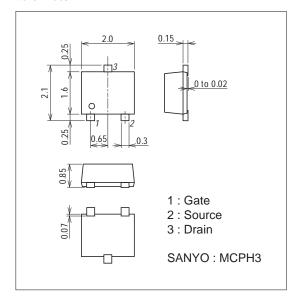
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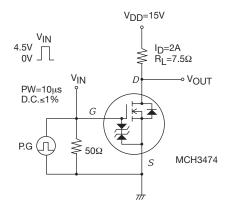
Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =2A, V <sub>GS</sub> =4.5V		38	50	mΩ
	R <sub>DS</sub> (on)2	ID=1A, VGS=2.5V		51	72	mΩ
	RDS(on)3	ID=0.5A, VGS=1.8V		80	130	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =10V, f=1MHz		430		pF
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		59		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =10V, f=1MHz		38		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		10		ns
Rise Time	tr	See specified Test Circuit.		41		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		36		ns
Fall Time	tf	See specified Test Circuit.		37		ns
Total Gate Charge	Qg	VDS=15V, VGS=4.5V, ID=4A		4.7		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		0.8		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		1.1		nC
Diode Forward Voltage	V <sub>SD</sub>	IS=4A, VGS=0V		0.82	1.2	V

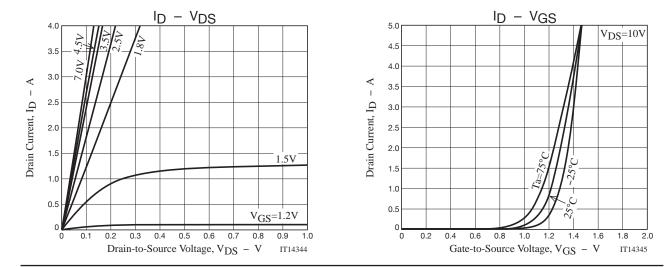
#### Package Dimensions

unit : mm (typ) 7019A-003

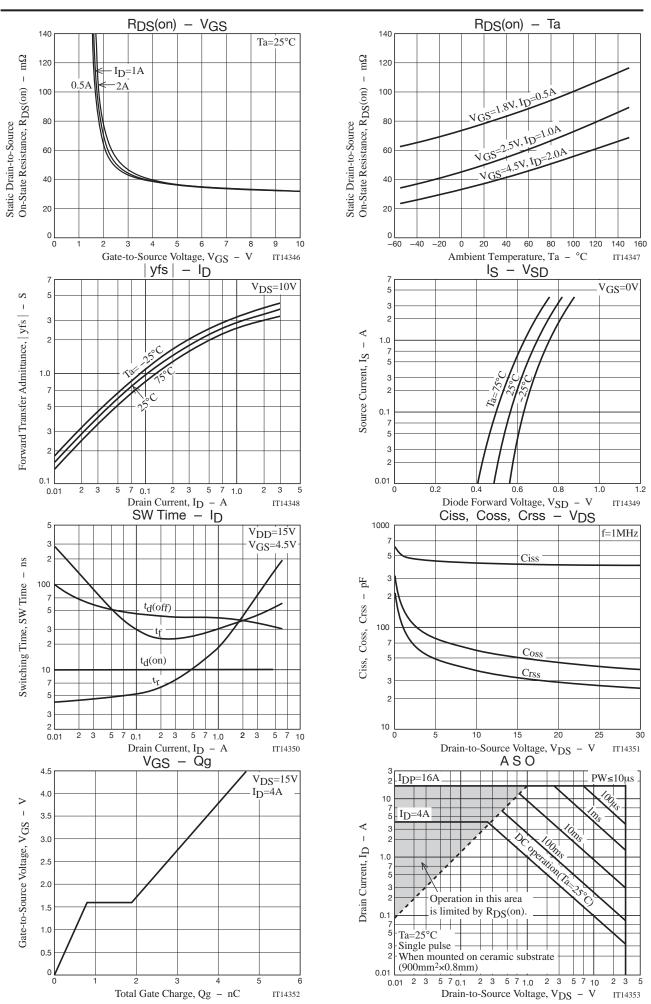


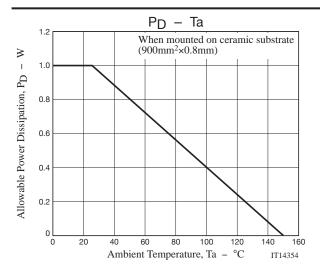
#### Switching Time Test Circuit





MCH3474





### Note on usage : Since the MCH3474 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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